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KAWABATA et al.(10) **Pub. No.: US 2015/0086912 A1**(43) **Pub. Date: Mar. 26, 2015**(54) **ACTINIC RAY-SENSITIVE OR
RADIATION-SENSITIVE RESIN
COMPOSITION, RESIST FILM AND
PATTERN FORMING METHOD USING THE
SAME, MANUFACTURING METHOD OF
SEMICONDUCTOR DEVICE, AND
SEMICONDUCTOR DEVICE****Publication Classification**(51) **Int. Cl.****G03F 7/038** (2006.01)
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526/256; 526/270; 526/287(71) Applicant: **FUJIFILM CORPORATION**, Tokyo
(JP)(72) Inventors: **Takeshi KAWABATA**, Haibara-gun
(JP); **Hideaki TSUBAKI**, Haibara-gun
(JP); **Hiroo TAKIZAWA**, Haibara-gun
(JP); **Natsumi YOKOKAWA**,
Haibara-gun (JP)(73) Assignee: **FUJIFILM CORPORATION**, Tokyo
(JP)(57) **ABSTRACT**(21) Appl. No.: **14/554,344**(22) Filed: **Nov. 26, 2014****Related U.S. Application Data**(63) Continuation of application No. PCT/JP2013/065770,
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There is provided an actinic ray-sensitive or radiation-sensitive resin composition comprising (P) a resin having a repeating unit (A) represented by the specific formula (I) capable of generating an acid on the side chain of the resin upon irradiation with an actinic ray or radiation, and a resist film formed with the actinic ray-sensitive or radiation-sensitive resin composition, and a pattern forming method comprising: exposing the resist film, and developing the exposed resist film, and a method for manufacturing a semiconductor device, containing the pattern forming method, and a semiconductor device manufactured by the manufacturing method of the semiconductor device.